MJE15034 (NPN), MJE15035 (PNP)

Complementary Silicon Plastic Power Transistors

TO−220, NPN & PNP Devices

Complementary silicon plastic power transistors are designed for use as high−frequency drivers in audio amplifiers.

Features

- High Current Gain − Bandwidth Product
- TO−220 Compact Package
- Epoxy meets UL 94 V−0 @ 0.125 in
- These Devices are Pb−Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	350	Vdc
Collector−Base Voltage	V_{CB}	350	Vdc
Emitter−Base Voltage	V_{EB}	5.0	Vdc
Collector Current − Continuous	I_C	4.0	Adc
Collector Current − Peak	I_{CM}	8.0	Adc
Base Current	I_B	1.0	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 50 0.40	 W W/°C
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	2.0 0.016	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C
ESD − Human Body Model	HBM	3B	V
ESD − Machine Model	MM	C	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	62.5	°C/W

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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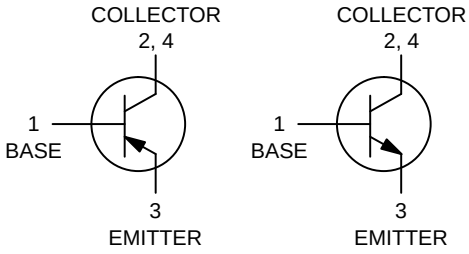
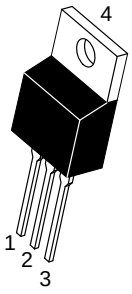
4.0 AMPERES
POWER TRANSISTORS
COMPLEMENTARY SILICON
350 VOLTS, 50 WATTS

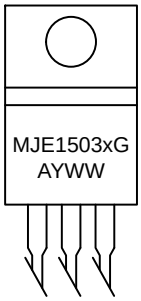
COMPLEMENTARY



MARKING DIAGRAM



TO−220
CASE 221A
STYLE 1



MJE1503x = Device Code
x = 4 or 5
A = Location Code
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE15034G	TO−220 (Pb−Free)	50 Units / Rail
MJE15035G	TO−220 (Pb−Free)	50 Units / Rail

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Sustaining Voltage (Note 1)	(I_C = 10 mAdc, I_B = 0)	$V_{CEO(sus)}$	350	−	Vdc
Collector Cutoff Current	(V_{CB} = 350 Vdc, I_E = 0)	I_{CBO}	−	10	μAdc
Emitter Cutoff Current	(V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	−	10	μAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain		h_{FE}			−
	(I_C = 0.1 Adc, V_{CE} = 5.0 Vdc)		100	−	
	(I_C = 0.5 Adc, V_{CE} = 5.0 Vdc)		100	−	
	(I_C = 1.0 Adc, V_{CE} = 5.0 Vdc)		50	−	
	(I_C = 2.0 Adc, V_{CE} = 5.0 Vdc)		10	−	
Collector−Emitter Saturation Voltage	(I_C = 1.0 Adc, I_B = 0.1 Adc)	$V_{CE(sat)}$	−	0.5	Vdc
Base−Emitter On Voltage	(I_C = 1.0 Adc, V_{CE} = 5.0 Vdc)	$V_{BE(on)}$	−	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain − Bandwidth Product (Note 2) (I_C = 500 mAdc, V_{CE} = 10 Vdc, f_{test} = 1.0 MHz)		f_T	30	−	MHz

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
2. $f_T = |h_{fe}| \bullet f_{test}$.

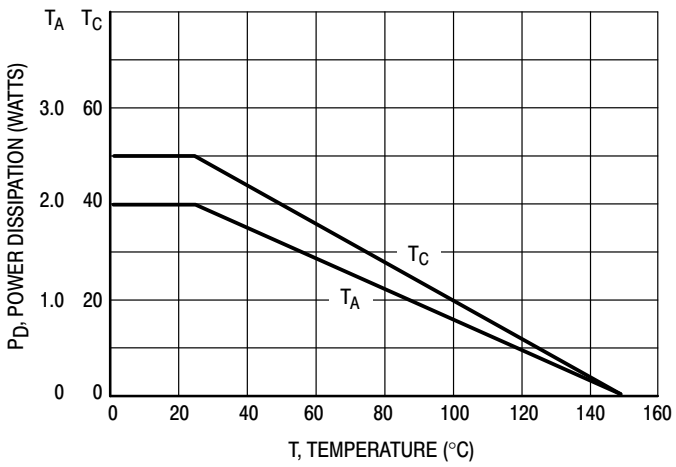


Figure 1. Power Derating

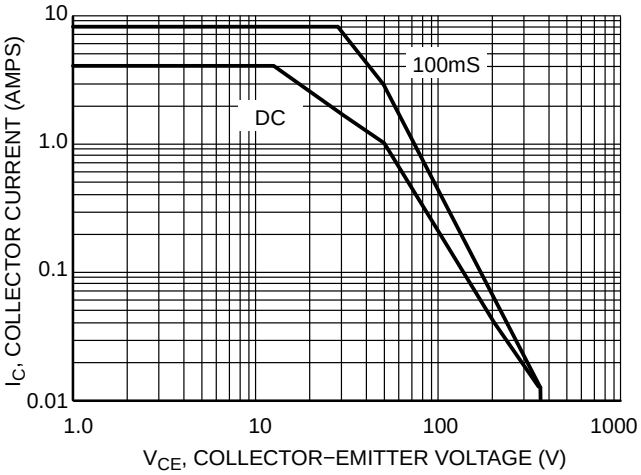


Figure 2. Active Region Safe Operating Area

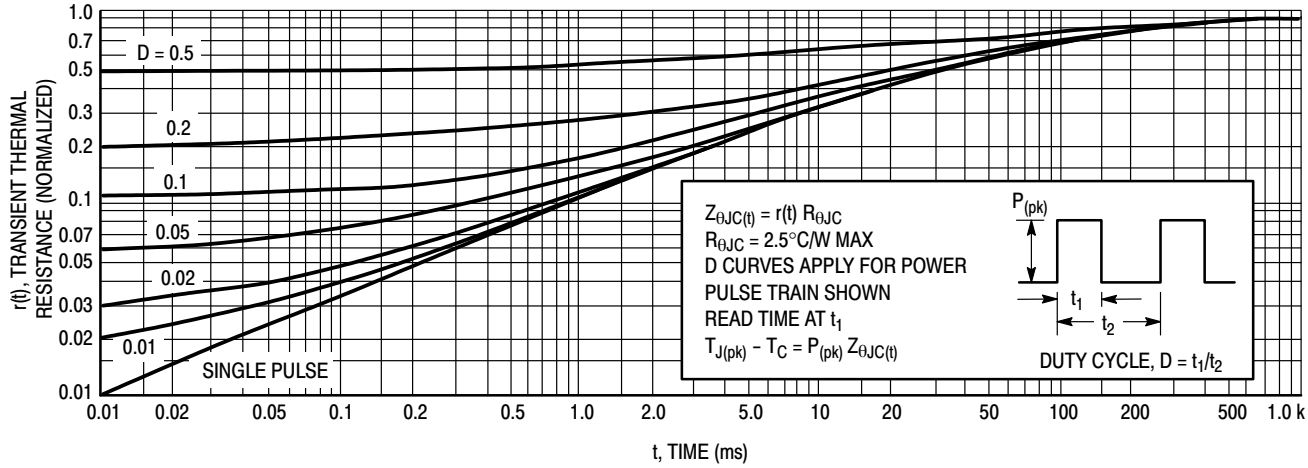


Figure 3. Thermal Response

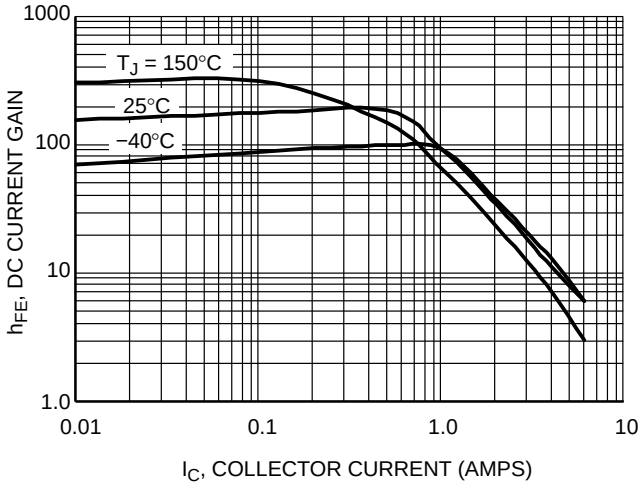


Figure 4. DC Current Gain, V_{CE} = 5.0 V
NPN MJE15034

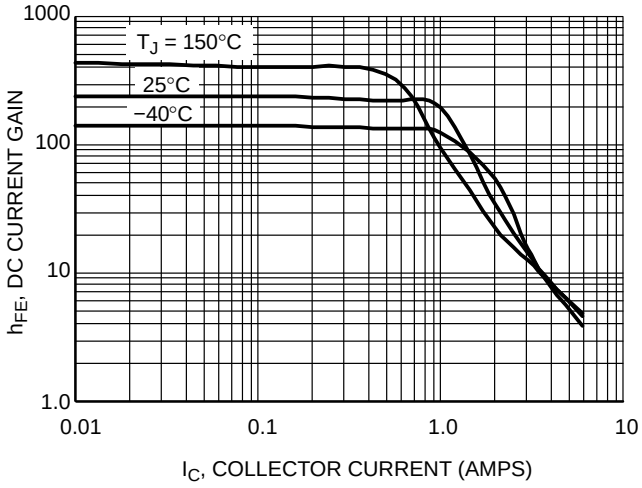


Figure 5. DC Current Gain, V_{CE} = 5.0 V
PNP MJE15035

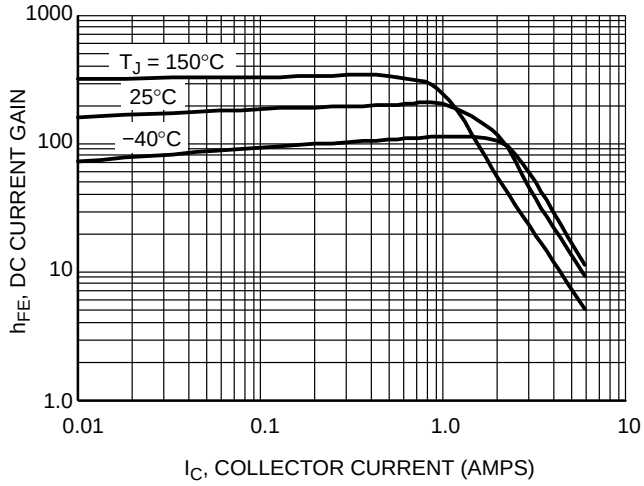


Figure 6. DC Current Gain, V_{CE} = 20 V
NPN MJE15034

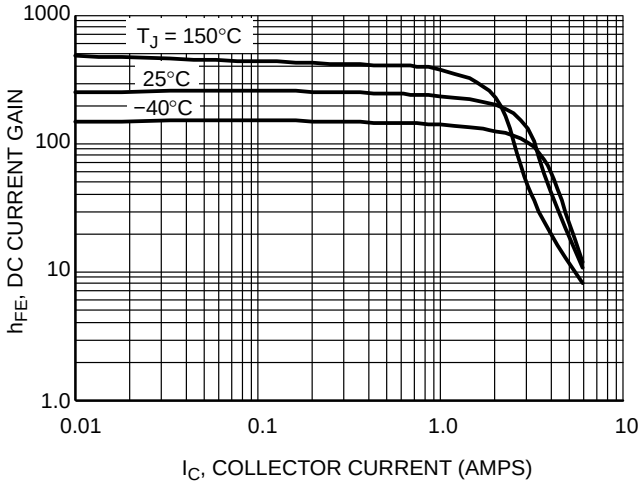


Figure 7. DC Current Gain, V_{CE} = 20 V
PNP MJE15035

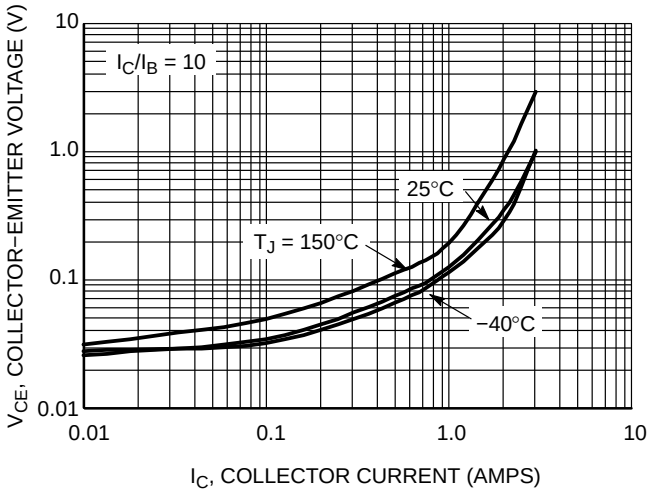


Figure 8. $V_{CE(sat)}$
NPN MJE15034

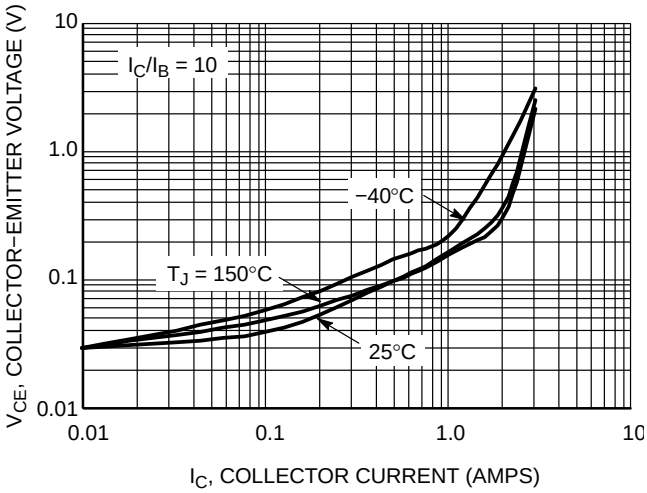


Figure 9. $V_{CE(sat)}$
PNP MJE15035

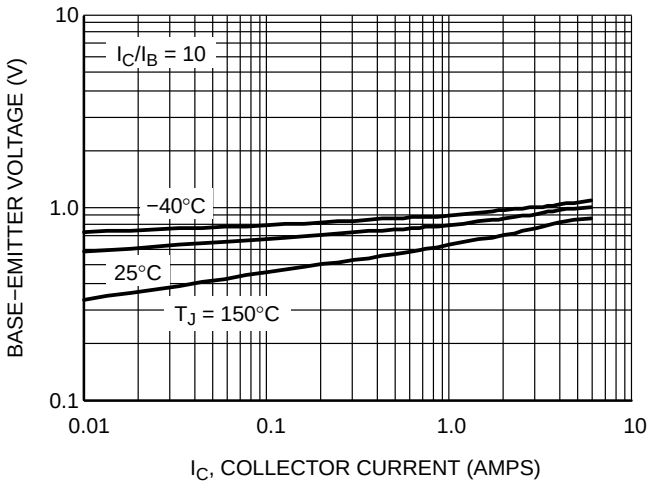


Figure 10. $V_{BE(sat)}$ NPN MJE15034

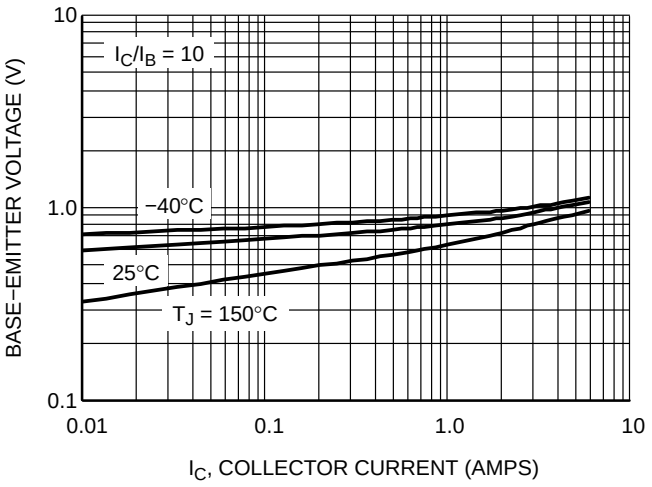


Figure 11. $V_{BE(sat)}$ PNP MJE15035

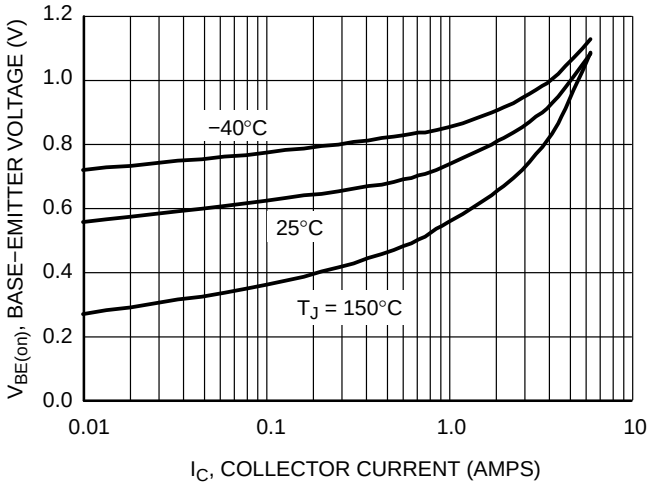


Figure 12. $V_{BE(on)}$ NPN MJE15034

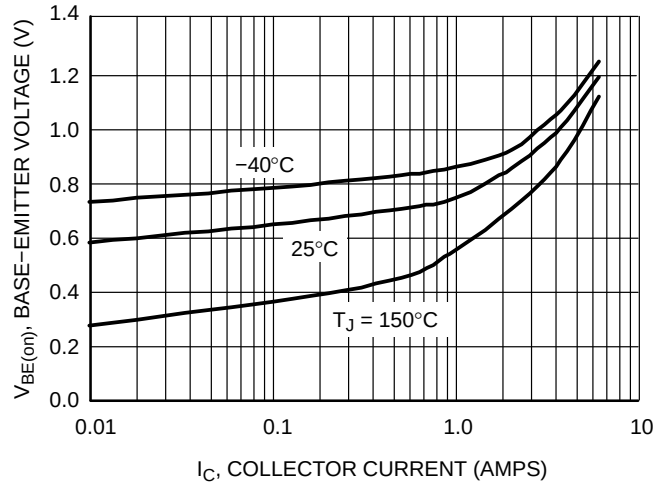


Figure 13. $V_{BE(on)}$ PNP MJE15035

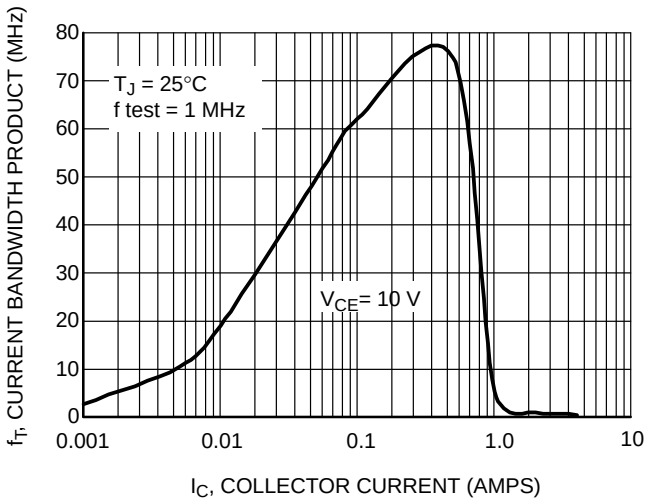


Figure 14. Typical Current Gain Bandwidth Product NPN MJE15034

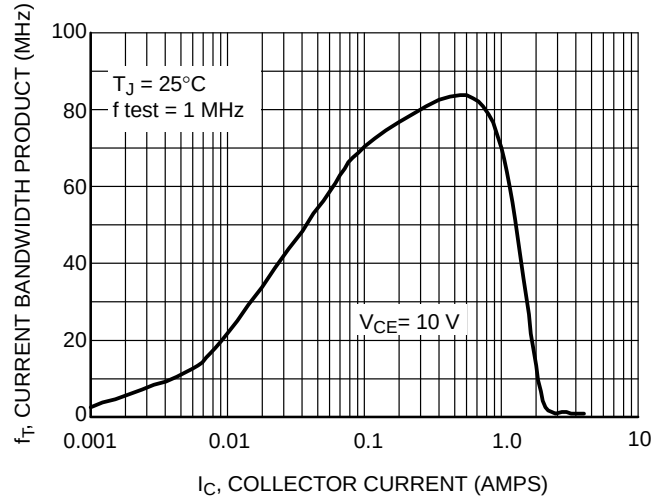
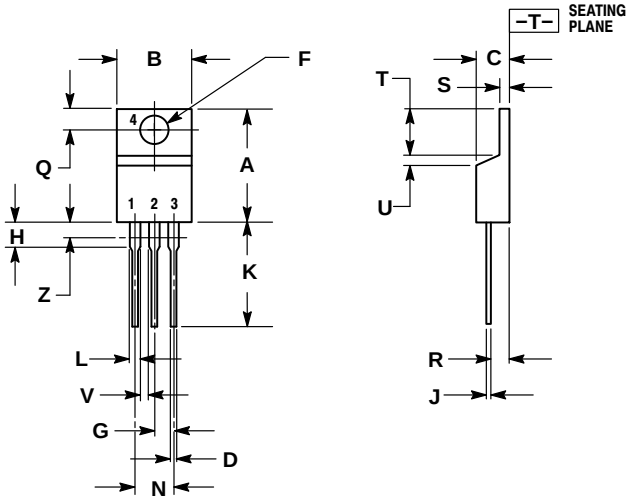


Figure 15. Typical Current Gain Bandwidth Product PNP MJE15035

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AG



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

PUBLICATION ORDERING INFORMATION

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MJE15034/D